

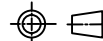

Note:

1. SUBSTRATE:IR MONO GRADE SI
2. GROWING METHOD:CZ
3. CLEAR APERTURE:95%
4. SURFACE QUALITY:S1&S2 60-40 SCRATCH-DIG
5. PARALLELISM:3ARCMIN
6. POWER:5 $\lambda/2$
7. IRREGULARITY:3 $\lambda/2$
8. COATING: NONE

9 FINE GRIND SURFACE

SPECIFICATIONS SUBJECT TO CHANGE
WITHOUT NOTICE

FOR INFORMATION ONLY
NOT FOR MANUFACTURE

DRAWING PROJECTION 		ALL DIMS IN	MM
DESIGNED	CHECKED	APPROVED	SCALE
			1:1
MATERIAL	Silicon	TITLE	SI IR-MONO ROUND WINDOW $\phi 20 * T2$
 本征晶体 INTRINSIC CRYSTAL		DWG NO	PSI01D002
		EDITION	1ST
		SHEET	1/1